

GENERAL DESCRIPITION

The MX22917 device is a 5.5V, 2A load switch in a 6 pin SOT23 package. To reduce voltage drop for low voltage and high current rails, the device implements a low resistance P channel MOSFET which reduces the drop out voltage across the device. The MX22917 device has a configurable slew rate which helps reduce or eliminate power supply droop because of large inrush currents. Furthermore, the device features a QOD pin, which allows the configuration of the discharge rate of VOUT after the switch is disabled. During shutdown, the device has very low leakage currents, thereby reducing unnecessary leakages for downstream modules during standby. Integrated control logic, driver, charge pump, and output discharge FET eliminates the need for any external components which reduces solution size and bill of materials count.

FEATURES

♦ Input voltage range: 1V to 5.5V

♦ Maximum continuous current: 2A

♦ On-resistance:

 $100 \text{m}\Omega$ at 5V input voltage (typical)

 $160 \text{m}\Omega$ at 1.8V input voltage (typical)

 $240m\Omega$ at 1V input voltage (typical)

♦ Ultra low power consumption

On state: 0.5uA typical

Off state: 10nA typical

♦ Soft start time can be adjusted

5V Ton=100us at CT open

5V Ton=2000us at C_T =1000pF

- ♦Output discharge time can be adjusted
- ♦ 6-Pin SOT23-6

APPLICATIONS

Industrial system

Wearable devices

Set-top box

Sales terminal

Blood glucose meter

GENERAL INFORMATION

Ordering information

Part Number	Description
MX22917T	SOT23-6, non-inverting
MX22917L	SOT23-6, inverting
MPQ	3000pcs

Package dissipation rating

Package	RθJA (°C/W)
SOT23-6	108.1

Absolute maximum ratings

Parameter	Value
VIN/VOUT/ON/QOD	-0.3 to 6V
IOUT MAX	2A
I _{PULSE} pulse<300us, 2% duty cycle	2.5A
Junction temperature	150°C
Storage temperature, Tstg	-55 to 150°C
Leading temperature (soldering, 10secs)	260℃
ESD Susceptibility HBM	±2000V

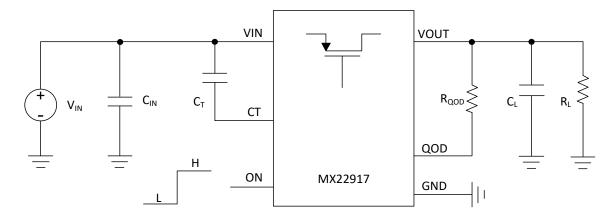
Stresses beyond those listed in Absolute Maximum Ratings may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect reliability. Functional operation of the device at any conditions beyond those indicated in the Recommended Operating Conditions section is not implied.

Recommended operating condition

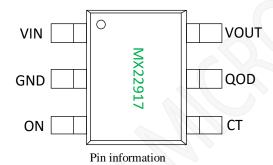
Symbol	Parameter	Range
VDD	VDD supply	1-5.5V
Junction temperature		-40~125°C
P_{D_MAX}	Power dissipation	0.59W



TYPICAL APPLICATION



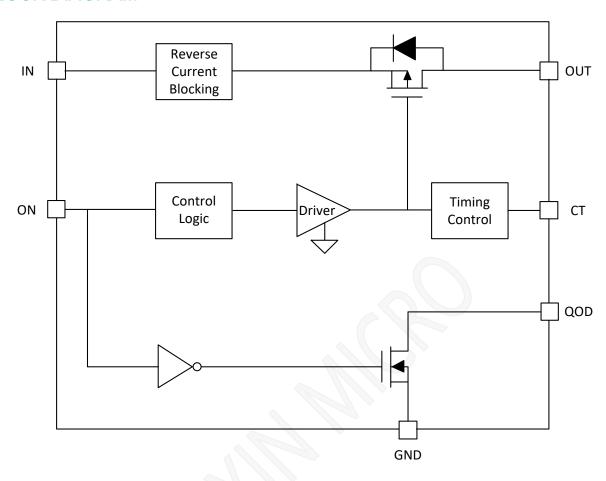
TERMINAL ASSIGMENTS



PIN NO.	PIN name	Description
1	VIN	Load switch input
2	GND	The device ground
3	ON	Active high switch control input (MX22917T) . Do not leave floating.
4	CT	Switch slew rate control. Connect capacitor from this pin to VIN to increase output slew rate and turn on time. Can be left floating for fastest timing.
5	QOD	Quick output discharge pin. This functionality can be enabled in one of three ways: Placing an external resistor between VOUT and QOD Tying QOD directly to VOUT and using the internal resistor value (RPD) Disabling QOD by leaving this pin floating
6	VOUT	Load switch output.



BLOCK DIAGRAM





Electrical characteristics

(TA=25°C, VDD=1.0V to 5.5V, unless otherwise noted)

Symbol	Parameter	Test condition	Min	Тур.	Max	Unit
POWER SUI	PPLY					
-	AND O AND MENT OF THE CONTROL OF	-40°C to +85°C		0.5	1.0	μA
I _{Q_} VIN	VIN Quiescent current, VOUT=OPEN	-40°C to +125°C			1.2	μA
	AND GLOVE OVER AN AND AND	-40°C to +85°C		10	100	nA
_	VIN Shutdown current, VOUT=GND MX22917	-40°C to +125°C			250	nA
I _{SD_VIN}	LIDI GLADA LIGHT ON DAMAGATI	-40°C to +85°C		175	300	nA
	VIN Shutdown current, VOUT=GND MX22917L	-40°C to +125°C			400	nA
ENABLE PII	N (ON)					
	ON pin leakage, Enabled MX22917	-40°C to +125°C	-10		10	nA
Ion	ON pin leakage, Enabled MX22917L	Current, VOUT=GND MX22917L	20	nA		
R _{PD}	Smart pulldown resistance, V _{ON} ≤V _{IL}	-40°C to +105°C		750		kΩ
REVERSE C	URRENT BLOCKING (RCB)					
IRCB	RCB Activation Current, VOUT>VIN	-40°C to +125°C		-1	-2	A
tRCB	RCB Activation time, VOUT>VIN+200mV	-40°C to +125°C		10		μs
VRCB	RCB Release Voltage, VOUT>VIN	-40°C to +125°C		25		mV
III D CD	VIN Reverse Leakage Current, 0V≤VIN+VRCB≤	1000 1 1050				
IIN_RCB	VOUT	-40 C to +105 C	-1			μA
QUICK OUT	PUT DISCHARGE (QOD)					
QOD	Output discharge resistance, disabled	-40°C to +105°C		150		Ω
ON STATE R	RESISTANCE (RON)					
	TOTAL COS A MAN SON	25℃		100	120	mΩ
		-40°C to +85°C			130	$m\Omega$
	IOUT=200mA, VIN=5.0V	-40°C to +105°C			140	mΩ
		-40°C to +125°C			145	mΩ
		25℃		110	130	$m\Omega$
	IOUT 200 A VIN 2 CV	-40°C to +85°C			150	$m\Omega$
	IOUT=200mA, VIN=3.6V	-40°C to +105°C			160	$m\Omega$
		-40°C to +125°C			165	mΩ
		25℃		150	170	$m\Omega$
D	TOLER 200 A MIN 1 0M	-40°C to +85°C			185	mΩ
R _{ON}	IOUT=200mA, VIN=1.8V	-40°C to +105°C			195	mΩ
		-40°C to +125°C			210	mΩ
		25℃		200	230	mΩ
	LOUTE 200 A. AVIN 1 237	-40°C to +85°C			265	mΩ
	IOUT=200mA, VIN=1.2V	-40°C to +105°C			280	mΩ
		-40°C to +125°C			300	mΩ
		25℃		240	320	mΩ
	IOUT 200 A VIN 1 0V	-40°C to +85°C			360	mΩ
	IOUT=200mA, VIN=1.0V	1000 1 10500			200	
		-40°C to +105°C			380	$\mathrm{m}\Omega$

Note: OUT is tied to VDD from a small resistor



Switching characteristics

(TA=25°C, VDD=1.0V to 5.5V with a load of CL=1 μ F and RL=10 Ω , unless otherwise noted)

Symbol	Parameter	Test condition	Min	Тур.	Max	Unit
POWER SUPPLY						
		$C_T = OPEN$		120		μs
	VIN=5.0V	$C_T \geqslant 100 pF$	0	3	6	μs/pF
(ON	VIN 2 CV	$C_T = OPEN$		140		μs
tON turn on time	VIN=3.6V	$C_T \geqslant 100 pF$	0	2.7	6	μs/pF
turn on time	VIN=1.8V			150		μs
	VIN=1.2V			160		μs
	VIN=1.0V			230		μs
	VIN FOU	$C_T = OPEN$		60		μs
	VIN=5.0V	$C_T \geqslant 100 pF$		1		μs/pF
T	VIN=3.6V	$C_T = OPEN$		70		μs
T _R		$C_T \geqslant 100 pF$		0.8		μs/pF
output rise time	VIN=1.8V			65		μs
	VIN=1.2V			50		μs
	VIN=1.0V			60		μs
	VIN=5.0V	$C_T = OPEN$		40		mV/μs
		$C_T \geqslant 100 pF$		1700		(mV/µs)*pF
T	VIN=3.6V	$C_T = OPEN$		25		mV/μs
T _{SR} Turn on slew rate (1)	VIIN=3.6 V	$C_T \geqslant 100 pF$	OpF			(mV/µs)*pF
Turn on siew rate	VIN=1.8V			12		mV/μs
	VIN=1.2V			7.5		mV/μs
	VIN=1.0V			4.5		mV/μs
Toff Turn off time				10		μs
	$R_L=10\Omega$	C _L =1µF, R _{QOD} =Short		22		μs
T _{FALL}		C _L =10µF, R _{QOD} =Short		3.8		ms
Output fall time (2)	$R_{\rm L} = { m OPEN}$	$C_L=10\mu F, R_{QOD}=100\Omega$		5.9		ms
		C _L =220µF, R _{QOD} =Short	72		ms	

⁽¹⁾ TSR is the fastest slew rate during the turn on time

⁽²⁾ Output may not discharge completely id QOD is not connected to VOUT.

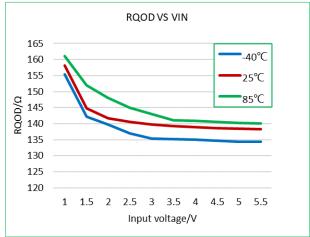
VON VS VIN

VON_H

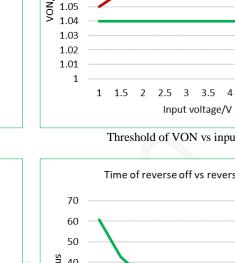
VON L



Characteristic plots



Internal quick discharge resistance vs input voltage



1.1

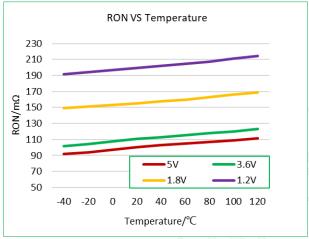
1.09

1.08

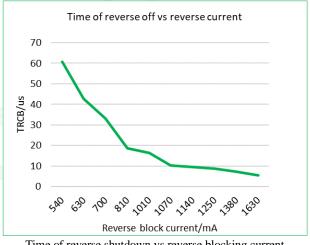
1.07

1.06

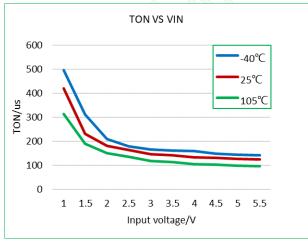
Threshold of VON vs input voltage



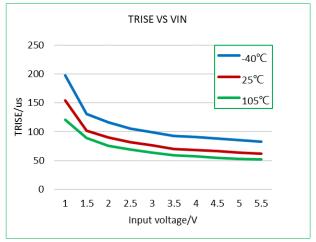
Internal PMOS on resistance vs temperature



Time of reverse shutdown vs reverse blocking current

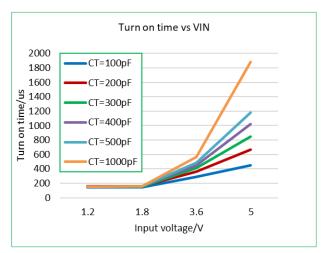


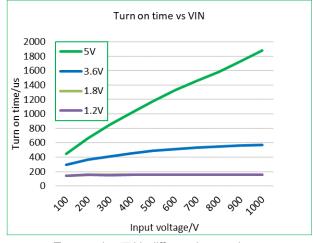
The turn on time vs input voltage (CT open)



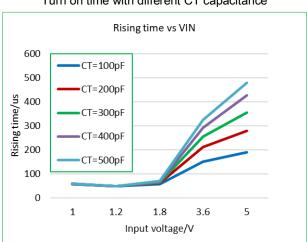
The rising time vs input voltage (CT open)



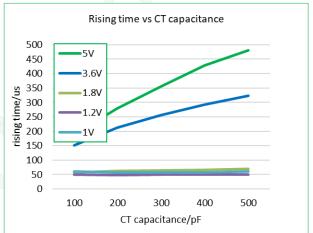




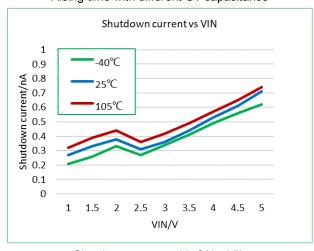
Turn on time with different CT capacitance



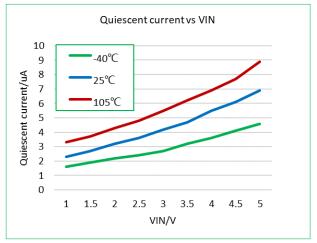
Turn on time with different input voltage



Rising time with different CT capacitance



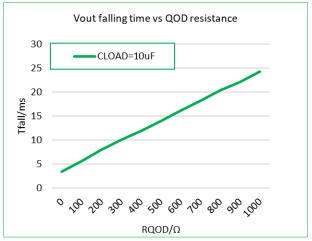
Rising time with different input voltage



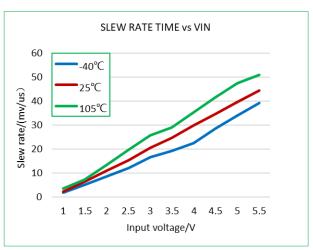
Shutdown current with ON ≤ VIL

Quiescent current with ON ≥ VIH

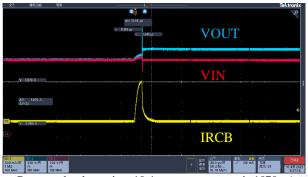




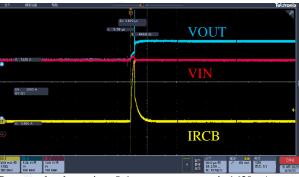
The VOUT falling time when load capacitor is 10uF



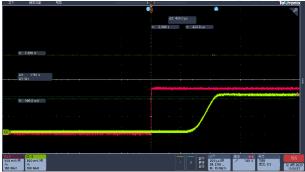
Slew rate time vs input voltage (CT open)



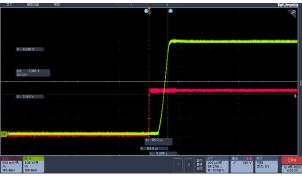
Reverse shutdown time 10.4us reverse current is 1070mA



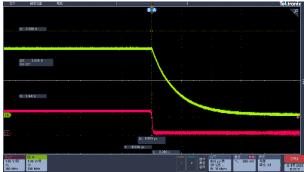
Reverse shutdown time 5.6us reverse current is 1630mA



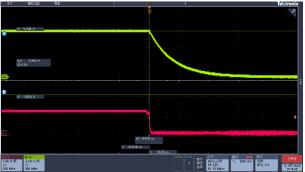
Turn on time when input is 1V (CT open)



Turn on time when input is 5V (CT open)



Turn off time when input is 3.6V (QOD short)



Turn off time when input is 5V (QOD short)



Operation description

The MX22917 device is a 5.5V, 2A load switch in a 6 pin SOT23 package. To reduce voltage drop for low voltage and high current rails, the device implements a low resistance P channel MOSFET which reduces the drop out voltage across the device. The MX22917 device has a configurable slew rate which helps reduce or eliminate power supply drop because of large inrush currents. Furthermore, the device features a QOD pin, which allows the configuration of the discharge rate of VOUT after the switch is disabled. During shutdown, the device has very low leakage currents, thereby reducing unnecessary leakages for downstream modules during standby. Integrated control logic, driver, charge pump, and output discharge FET eliminates the need for any external components which reduces solution size and bill of materials count.

On and off control

The ON pin controls the state of the switch. The ON pin is compatible with standard GPIO logic threshold so it can be used in a wide variety of applications. The MX22917 is enabled when the voltage applied to the ON pin is pulled above $V_{\rm IH}$, while the MX22917L is enabled when the voltage is below $V_{\rm IL}$.

When power is first applied to VIN, a smart pulldown is used to keep the ON pin from floating until system sequencing is complete. After the ON pin is deliberately driven high, the smart pulldown is disconnected to prevent unnecessary power loss. The next table shown when the ON pin smart pulldown is active.

VON	Pulldown
≪VIL	Connected
≥VIH	Disconnected

Turn on time and adjustable slew rate

A capacitor to VIN on the CT pin sets the slew rate of VOUT. The CT capacitor voltage ramps until shortly after the switch is turned on and VOUT becomes stable.

Leaving the CT pin open results in the highest slew rate and fastest turn on time. These values can be found in the switching

characteristics table. For slower slew rates the required CT capacitor can be found using the next formular:

 $CT = (Slew Rate) \div SR_{ON}$

Where

Slew Rate = desired slew rate (mV/us)

CT = the capacitance value on the CT pin (pF)

 $SR_{ON} = Slew$ rate constant from table

The total turn on time has a direct correlation to the output slew rate. The fastest turn on time, with CT pin open, can be found in the switching characteristics. For slower slew rates, the resulting turn on time can be found with:

Turn on time = $CT \times t_{ON}$

Where

Turn on time = total time from enable until VOUT rises to 90% of Vin (us)

CT= the capacitance value of the CT pin (pF)

ton = turn on time constant (us/pF)

Fall time and quick output discharge

The MX22917 device includes a QOD pin that can be figured in one of three ways:

- QOD pin shorted to VOUT pin. Using this method, the discharge rate after the switch becomes disabled is controlled with the value of internal resistance QOD.
- QOD pin connected to VOUT pin using an external resistor R_{QOD}. After the switch becomes disabled, the discharge rate is controlled by the value of the total discharge resistance. To adjust the total discharge resistance, the next formula can be used:

 $R_{DIS} = QOD + R_{QOD}$

Where

 R_{DIS} = total output discharge resistance (Ω)

QOD = internal pulldown resistance (Ω)

 $R_{\rm QOD} = {\rm external}$ resistance placed between the VOUT and QOD pins (Ω)

ullet QOD pin is unused and left floating. Using this method, there is no quick output discharge functionality, and the output capacitance (C_L). To calculate the approximate fall time of VOUT use:

 $t_{FALL}=2.2\times(R_{DIS}\parallel R_L)\times C_L$

QOD when system power removed

The adjustable QOD can be used to control the power down sequencing of a system even when the system power supply is removed. When the power is removed, the input capacitor



discharges at VIN. Past a certain VIN level, the strength of the RPD is reduced. If there is still remaining charge on the output capacitor, this results in longer fall times.

Full time reverse current blocking

In a scenario where the device is enabled and VOUT is greater than VIN there is potential for reverse current to flow through the pass FET or the body diode. When the reverse current threshold (I_{RCB}) is exceeded, the switch is disabled within t_{RCB} . The switch remains off and block reverse current as long as the reverse voltage condition exists. After VOUT has dropped below the V_{RCB} release threshold the device turns back on with slew rate control.

Device functional modes

The next table describes the connection of the VOUT pin depending on the state of the ON pin as well as the various QOD pin configurations.

ON	QOD configuration	VOUT
L	Connected to VOUT with	GND
	R_{QOD}	
L	Tied to VOUT directly	GND
L	Left opening	Floating
Н	Connected to VOUT with	VIN
	R _{QOD}	
Н	Tied to VOUT directly	VIN
Н	Left opening	VIN

MX22917

ON	QOD configuration	VOUT
L	Connected to VOUT with	VIN
	R _{QOD}	
L	Tied to VOUT directly	VIN
L	Left opening	VIN
Н	Connected to VOUT with	GND
	RQOD	
Н	Tied to VOUT directly	GND
Н	Left opening	Floating

MX22917L

Power supply recommendations

The device is designed to operate with a VIN range of 1V to 5.5V. The VIN power supply must be well regulated and placed as close to the device terminal as possible. The power supply must be able to withstand all transient load current steps. In most situations, using an input capacitance of 1uF is sufficient to prevent the supply voltage from dipping when switch is turned on. In case where the power supply is slow to respond to a large transient current or large load current step, additional bulk capacitance can be required on the input.

Thermal considerations

The maximum IC junction temperature must be restricted to

 125° C under normal operating conditions. To calculate the maximum allowable dissipation, PD(MAX) for a given output current and ambient temperature, use formula:

$$P_{D(MAX)} = \frac{T_{J(MAX)} - T_A}{\theta_{JA}}$$

Where

 $P_{D(MAX)}$ = maximum allowable power dissipation

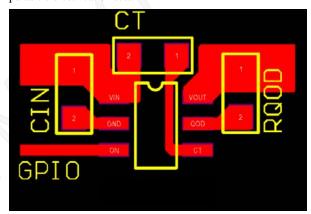
 $T_{J(MAX)}$ = maximum allowable junction temperature

 T_A = ambient temperature of the device

 θ_{JA} = junction to air thermal impedance.

Layout guidelines

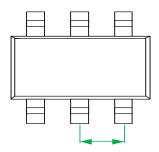
For best performance, all traces must be as short as possible. To be most effective, the input and output capacitors must be placed as close to the device to minimize the effects that parasitic electrical effects.





Ordering PN	Package	Vendor	Product	MOQ
MX22917T	SOT23-6	Wuxi Maxin micro	Load switch 1-5.5v	3K
MX22917L	SOT23-6	Wuxi Maxin micro	Load switch 1-5.5v	3K

Package information



SYMBOL		MILLIMETER	S		INCHES	
SIMBOL	MIN	NOM	MAX	MIN	NOM	MAX
A	1.070	1.160	1.250	0.042	0.046	0.049
A1	0.02		0.10	0.001		0.004
A2	1.050	1.100	1.150	0.041	0.043	0.045
A3	0.60	0.65	0.70	0.024	0.026	0.028
D	2.820	2.920	3.020	0.111	0.115	0.119
Е	2.650	2.800	2.950	0.104	0.110	0.116
E1	1.500	1.600	1.700	0.059	0.063	0.067
e		0.95BSC			0.037BSC	
e1		1.90BSC			0.075BSC	
L	0.300		0.500	0.012		0.020
θ	0		4°	0		4°

SOT23-6L for MX22917



Restrictions on Product Use

- ♦ MAXIN micro is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing MAXIN products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such MAXIN products could cause loss of human life, bodily injury or damage to property.
- ◆ In developing your designs, please ensure that MAXIN products are used within specified operating ranges as set forth in the most recent MAXIN products specifications.
- ◆ The information contained herein is subject to change without notice.

Version update information

V10 preliminary version

V11 characteristics plot and test waveform were added